# 2SC4591

## Silicon NPN Epitaxial

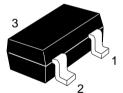
# **HITACHI**

#### **Application**

UHF / VHF wide band amplifier

#### Outline

MPAK



- 1. Emitter
- 2. Base
- 3. Collector



## 2SC4591

### **Absolute Maximum Ratings** ( $Ta = 25^{\circ}C$ )

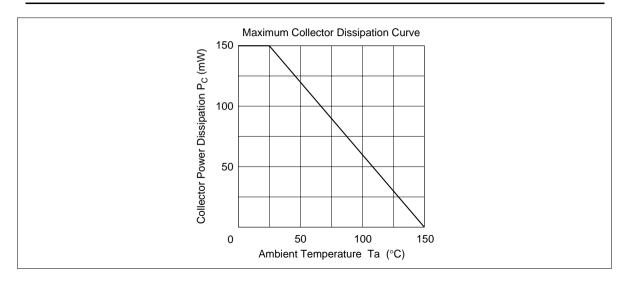
Item	Symbol	Ratings	Unit
Collector to base voltage	$V_{CBO}$	15	V
Collector to emitter voltage	$V_{\text{CEO}}$	9	V
Emitter to base voltage	$V_{EBO}$	1.5	V
Collector current	I <sub>c</sub>	50	mA
Collector power dissipation	P <sub>c</sub>	150	mW
Junction temperature	Tj	150	°C
Storage temperature	Tstg	-55 to +150	°C

### **Electrical Characteristics** (Ta = 25°C)

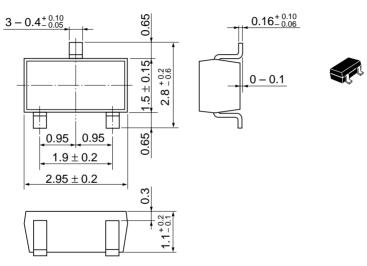
Item	Symbol	Min	Тур	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	15	_	_	V	$I_{\rm C} = 10 \ \mu A, \ I_{\rm E} = 0$
Collector cutoff current	I <sub>CBO</sub>	_	_	1	μΑ	$V_{CB} = 12 \text{ V}, I_{E} = 0$
	I <sub>CEO</sub>	_	_	1	mA	V <sub>CE</sub> = 9 V, R <sub>BE</sub> = ∞
Emitter cutoff current	I <sub>EBO</sub>	_	_	10	μΑ	$V_{EB} = 1.5 \text{ V}, I_{C} = 0$
DC current transfer ratio	$h_{FE}$	40	120	250	_	$V_{CE} = 5 \text{ V}, I_{C} = 20 \text{ mA}$
Collector output capacitance	Cob	_	8.0	1.5	pF	$V_{CB} = 5 \text{ V}, I_{E} = 0,$ f = 1MHz
Gain bandwidth product	f <sub>T</sub>	6.5	9.0	_	GHz	$V_{CE} = 5 \text{ V}, I_{C} = 20 \text{ mA}$
Power gain	PG	9.5	12.5	_	dB	$V_{CE} = 5 \text{ V}, I_{C} = 20 \text{ mA},$ f = 900 MHz
Noise figure	NF	_	1.2	2.5	dB	$V_{CE} = 5 \text{ V}, I_{C} = 5 \text{ mA},$ f = 900 MHz

Note: Marking is "XM-".

See characteristic curve of 2SC4592



Unit: mm



Hitachi Code	MPAK
JEDEC	_
EIAJ	Conforms
Weight (reference value)	0.011 g

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